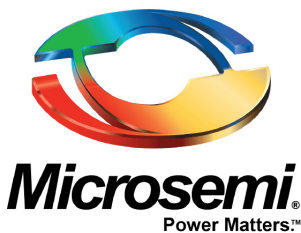


Le87614
PLC Dual Channel Class AB Line Driver
Line Driver BD870 Series

Preliminary Datasheet





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1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision 1.0

Revision 1.0 was the first publication of this document.

2 Overview

The Le87614 is a dual channel differential amplifier designed to work in Home Plug Alliance HPAV2 systems with very low power dissipation.

The Le87614 contains two pairs of wide-band amplifiers designed with Microsemi's HV15 Bipolar SOI process for low power consumption.

The line driver gain is fixed internally. The amplifiers are powered from a single supply.

The device can be programmed to one of three preset bias levels or to a disable state. Each channel can be controlled independently. The control pins respond to input levels that can be generated with a standard tri-state GPIO. Two pairs of switches allow receiver loads to be disconnected during transmit mode, saving driver power.

The Le87614 is available in a 28-pin, 4 mm x 5 mm QFN package with an exposed pad for enhanced thermal conductivity.

2.1 Features

- 28-pin, 4 mm x 5 mm QFN package
- Very low power dissipation
 - Class AB operation
- 4 programmable states
- No external gain resistors required
- RoHS compliant

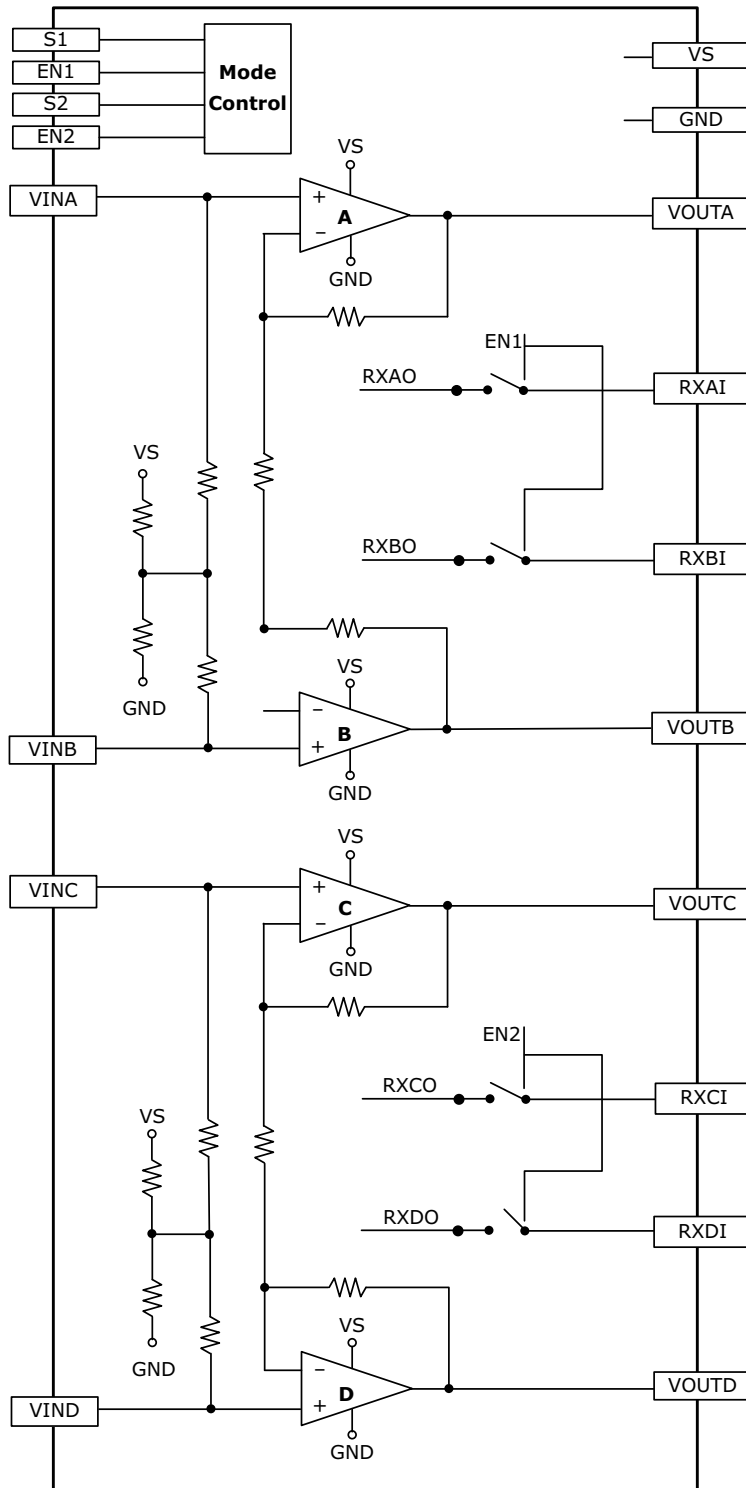
2.2 Target Applications

- Power Line Communications
- Home Networking
- HPNA
- G.HN

2.3 Block Diagram

The following figure shows the Le87614 block diagram.

Figure 1 • Block Diagram



3 Functional Descriptions

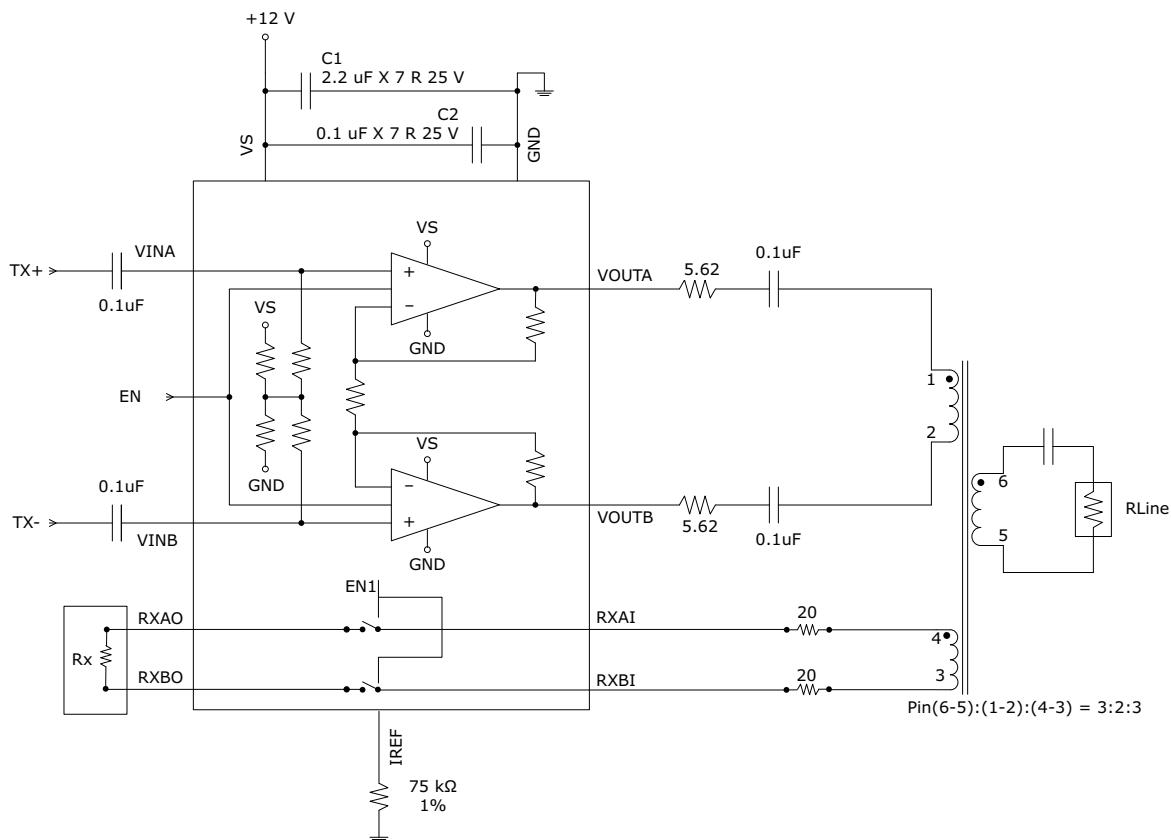
3.1 Applications

The Le87614 integrates two sets of high-power line driver amplifiers designed for low distortion of signals up to 106 MHz.

3.1.1 Block Diagram

The following figure shows an application circuit of channel 1 with amplifiers A and B in transmission.

Figure 2 • Application Circuit Diagram



3.1.1.1 Input Considerations

The driving source impedance should be less than 100 nH to avoid any ringing or oscillation.

3.1.1.2 Output Driving Considerations

The internal metalization is designed to carry up to about 100 mA of steady DC current and there is no current limit mechanism. The device does feature integrated thermal shutdown protection with hysteresis. It is recommended that series resistors are used to drive lines.

3.1.1.3 Power Supplies and Component Placement

The power supplies should be well bypassed close to the Le87614 device. A 2.2 μF tantalum capacitor and a 0.1 μF ceramic capacitor are recommended for the VS supply.

4 Electrical Specifications

This section provides the DC characteristics, AC characteristics, recommended operating conditions, and stress ratings for the Le87614 device.

Typical Conditions: $V_S = +12\text{ V}$, $R_{REF} = 75\text{ k}\Omega$, and $T_A = 25\text{ }^\circ\text{C}$. For more information, see [Figure 3](#), page 6.

Min/Max Parameters: $T_A = 0\text{ to }+85\text{ }^\circ\text{C}$

The following tables show the electrical specifications.

Table 1 • Supply Current Characteristics

| Symbol | Parameter Description | Condition | Min | Typ | Max | Unit |
|----------|------------------------------|--------------------|-----|------|-----|------|
| I_{VS} | Supply current (per channel) | Full power state | 17 | 23 | 29 | mA |
| | | Medium power state | 11 | 19 | 23 | mA |
| | | Low power state | 5 | 10.5 | 15 | mA |
| | | Disable state | | 1 | 1.5 | mA |

Table 2 • Control Input (S1, S2, EN1, EN2) Specifications

| Symbol | Parameter Description | Condition | Min | Typ | Max | Unit |
|----------|-------------------------------|-----------|------|-----|-----|------|
| V_{IH} | Input high voltage | | 2.0 | 3.3 | 3.6 | V |
| V_{IM} | Input middle voltage (S1, S2) | | | 1.5 | | V |
| V_{IL} | Input low voltage | | -0.3 | 0 | 0.8 | V |
| | Enable time | | | 500 | | ns |

Table 3 • Amplifier Characteristics

| Symbol | Parameter Description | Condition | Min | Typ | Max | Unit |
|----------|-----------------------|------------------------------------|-----|-----|-----|------------|
| | Differential gain | Full power state, V_{OUT}/V_{IN} | 8.2 | 8.7 | 9.0 | V/V |
| | Bandwidth, -3 dB | Full power state | | 200 | | MHz |
| | | Medium power state | | 200 | | MHz |
| | | Low power state | | | 115 | |
| V_O | Output voltage | | | 10 | | V |
| I_{O1} | Output current | | 150 | | | mA |
| Z_I | Input impedance | Differential | 13 | 15 | 18 | k Ω |

1. Not tested in production. Guaranteed by characterization and design.

Table 4 • Amplifier Dynamic Characteristics

| Symbol | Parameter Description | Condition | Min | Typ | Max | Unit |
|--------------------|------------------------------|----------------|-----|-----|-----|------------------------|
| Noise ¹ | Input referred noise | 2 – to 106 MHz | | 9 | 15 | nV/ $\sqrt{\text{Hz}}$ |
| TSD | Thermal shutdown temperature | | | 170 | | °C |

1. Not tested in production. Guaranteed by characterization and design.

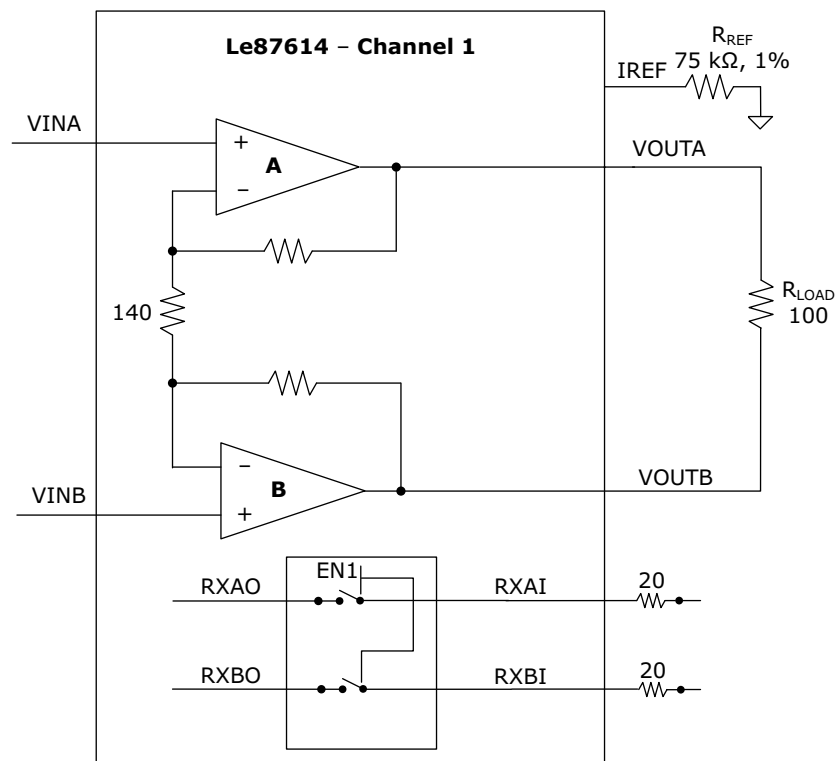
Table 5 • Switch Characteristics

| Symbol | Parameter Description | Condition | Min | Typ | Max | Unit |
|------------------|----------------------------------|-----------|-----|-----|-----|------|
| R _{ON} | On resistance | EN = 0 | | 2 | | Ω |
| R _{OFF} | Off resistance | EN = 1 | 15 | | | kΩ |
| V _{IM} | Common mode voltage ¹ | | | 4.1 | | V |

1. Not tested in production. Guaranteed by design and characterization.

The following figure shows the basic test circuit:

Figure 3 • Basic Test Circuit



4.1 State Control

S1, EN1 and S2, EN2 pins are used as combinatorial logic inputs to control the line driver operating states. For more information, see [Table 6](#) and [Table 7](#).

S1 and S2 are tri-state inputs that accept three operating levels. These pins have internal resistors tied to +1.5 V, which forces a middle logic input level when the control to these pins is tri-stated.

The following tables show channel 1 and channel 2 matrix.

Table 6 • Channel 1 Control Matrix

| S1 | EN1 | Transmit State | Receive State |
|------|-----|--------------------|---------------|
| X | 0 | Disable | Switch on |
| 0 | 1 | Enable low bias | Switch off |
| Open | 1 | Enable medium bias | Switch off |
| 1 | 1 | Enable full bias | Switch off |

Table 7 • Channel 2 Control Matrix

| S2 | EN2 | Transmit State | Receive State |
|------|-----|--------------------|---------------|
| X | 0 | Disable | Switch on |
| 0 | 1 | Enable low bias | Switch off |
| Open | 1 | Enable medium bias | Switch off |
| 1 | 1 | Enable full bias | Switch off |

4.1.1 Disable State

Amplifier bias current is removed. This is the lowest power state. Amplifier output is high impedance. Gain-setting feedback resistors are still connected across amplifier output pins, creating 1300 Ω differential impedance at pins.

4.1.2 Bias State

Line driver is active for transmission. States are different only in the amount of bias current to the amplifiers, and therefore power consumption. There is a trade-off between bias current and bandwidth.

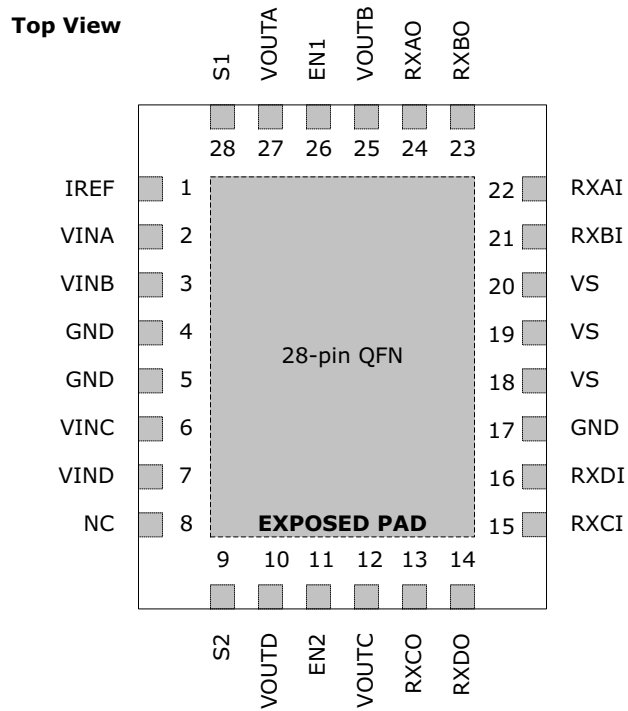
5 Pin Descriptions

The Le87614 device has 28 pins, which are described in this section.

5.1 Connection Diagram

The following illustration represents the pin diagram for the Le87614 device, as seen looking through the package from the top of it.

Figure 4 • Connection Diagram



Note:

The Le87614 device incorporates an exposed die pad on the underside of its package. The pad acts as a heat sink and must be connected to a copper plane through thermal via, for proper heat dissipation. It must be connected to GND.

5.1.1 Pin Description

The following table shows the functional pin descriptions for the Le87614 device.

Table 8 • Pin Descriptions

| Pin | Pin Name | Type | Description |
|-----|-------------|--------|--|
| 1 | IREF | Input | Device internal reference current. Connect a resistor (R_{REF}) to GND |
| 2 | VINA | Input | Non-inverting input of amplifier A |
| 3 | VINB | Input | Non-inverting input of amplifier B |
| 4 | GND | Ground | Reference ground |
| 5 | GND | Ground | Reference ground |
| 6 | VINC | Input | Non-inverting input of amplifier C |
| 7 | VIND | Input | Non-inverting input of amplifier D |
| 8 | NC | | No internal connection |
| 9 | S2 | Input | Channel 2 state control |
| 10 | VOUTD | Output | Amplifier D output |
| 11 | EN2 | Input | Enable channel 2 transmission |
| 12 | VOUTC | Output | Amplifier C output |
| 13 | RXCO | Output | Receive switch C output |
| 14 | RXDO | Output | Receive switch D output |
| 15 | RXCI | Input | Receive switch C input |
| 16 | RXDI | Input | Receive switch D input |
| 17 | GND | Ground | Reference ground |
| 18 | VS | Power | Power supply, +12 V |
| 19 | VS | Power | Power supply, +12 V |
| 20 | VS | Power | Power supply, +12 V |
| 21 | RXBI | Input | Receive switch B input |
| 22 | RXAI | Input | Receive switch A input |
| 23 | RXBO | Output | Receive switch B output |
| 24 | RXAO | Output | Receive switch A output |
| 25 | VOUTB | Output | Amplifier B output |
| 26 | EN1 | Input | Enable channel 1 transmission |
| 27 | VOUTA | Output | Amplifier A output |
| 28 | S1 | Input | Channel 1 state control |
| | Exposed pad | | Thermal conduction pad, must be grounded |

6 Package Information

6.1 Absolute Maximum Ratings

If the stress is above the values listed in [Table 9](#), it can cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods can affect device reliability.

The following table shows the absolute maximum ratings.

Table 9 • Absolute Maximum Ratings

| Names | Range |
|---|---|
| Storage temperature | $-65 \leq T_A \leq +150 \text{ }^\circ\text{C}$ |
| Operating junction temperature ⁽¹⁾ | $-40 \leq T_j \leq +150 \text{ }^\circ\text{C}$ |
| VS with respect to GND | -0.3 V to +16 V |
| Control inputs with respect to GND | -0.3 V to 4 V |
| Continuous driver output current | 100 mA |
| Maximum device power dissipation, continuous ⁽²⁾ - $T_A = 85 \text{ }^\circ\text{C}$, P_D | 1.0 W |
| Junction to ambient thermal resistance ^(2,3) , θ_{JA} | 36.0 $^\circ\text{C/W}$ |
| Junction to board thermal resistance ⁽²⁾ , θ_{JB} | 18.3 $^\circ\text{C/W}$ |
| Junction to case bottom (exposed pad) thermal resistance, $\theta_{JC(BOTTOM)}$ | 8.9 $^\circ\text{C/W}$ |
| Junction-to-top characterization parameter ⁽²⁾ , ψ_{JT} | 1.2 $^\circ\text{C/W}$ |
| ESD immunity (Human Body Model) | JESD22 class 2 compliant |
| ESD immunity (Charge Device Model) | JESD22 class IV compliant |

1. Continuous operation above 145 $^\circ\text{C}$ junction temperature may degrade device reliability.
2. For more information, see [Thermal Resistance](#), page 10
3. No air flow

6.1.1 Thermal Resistance

The thermal performance of a thermally enhanced package is assured through optimized printed circuit board layout. Specified performance requires that the exposed thermal pad be soldered to an equally sized exposed copper surface, which, in turn, conducts heat through multiple via to larger internal copper planes.

6.1.2 Package Assembly

The green package devices are assembled with enhanced, environmental compatible lead-free, halogen-free, and antimony-free materials. The leads possess a matte-tin plating, which is compatible with conventional board assembly processes or newer lead-free board assembly processes.

Refer to IPC/JEDEC J-Std-020 [Table 9](#) for recommended peak soldering temperature and [Table 10](#) for the recommended solder re-flow temperature profile.

6.1.3 Operating Ranges

Microsemi guarantees the performance of the Le87614 device over the 0 $^\circ\text{C}$ to 85 $^\circ\text{C}$ temperature range by conducting electrical characterization over each range and by conducting a production test with single insertion coupled with periodic sampling. These characterization and test procedures comply with the Telcordia GR-357-CORE generic requirements for assuring the reliability of components used in telecommunications equipment.

The following table shows the operating ranges.

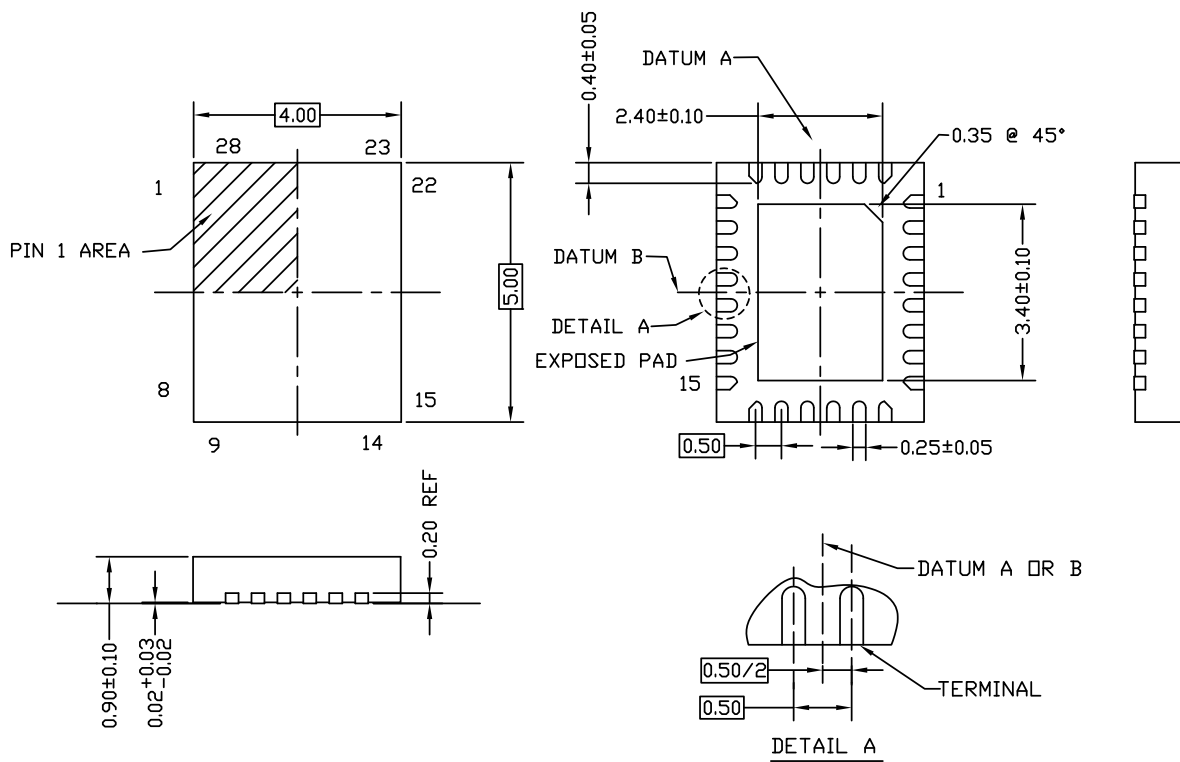
Table 10 • Operating Ranges

| Name | Unit | Range |
|---------------------|------------------------|---------------|
| Ambient temperature | T_A | 0 °C to 85 °C |
| Power supply | VS with respect to GND | 12 V \pm 5% |

6.2 Physical Dimension - 28-Pin Diagram

The following illustration shows the package drawing for the Le87614 device. The drawing contains the top view, bottom view, side view, dimensions, and tolerances.

Figure 5 • Package Drawing



7 Ordering Information

The following table lists the ordering information for the Le87614 device.

Table 11 • Ordering Information

| Part Order Number | Description |
|--------------------------|---|
| Le87614MQC | 28-pin, 4 mm x 5 mm QFN green package with an exposed pad Tray |
| Le87614MQCT | 28-pin, 4 mm x 5 mm QFN green package with an exposed pad Tape and reel |

Note: The green package meets RoHS 2 Directive 2011/65/EU of the European Council to minimize the environmental impact of electrical equipment.

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